AMENDED CLAIM SET

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- 8. (currently amended) A semiconductor field effect device having a gate dielectric and a
 gate, wherein said gate comprises a compound comprising Ta and N TaSiN disposed
 over said gate dielectric, wherein said compound TaSiN has a resistivity below about
 20mΩcm, and wherein in said compound the elemental ratio of N to Ta greater than
 about 0.9:1, and a workfunction between about 4.31eV and 4.4eV.
- 1 9. 11. (canceled)
- 1 12. (currently amended) The field effect device of claim 9 8, wherein in said TaSiN the Si 2 to Ta elemental ratio is between about 0.35 and 0.5 0.35:1 and 0.5:1.
- 1 13. (currently amended) The field effect device of claim 12, wherein said TaSiN has an a substantially amorphous material structure.
- 1 14. (canceled)
- 1 15. (original) The field effect device of claim 8, wherein said gate dielectric has an Serial No.: 10/712,575; Docket No.: YOR920030438US1 Page 5 of 10

1	equivalent oxide thickness of less than about 5nm.
1	16. (original) The field effect device of claim 15, wherein said gate dielectric has an
2	equivalent oxide thickness of less than about 2mm.
1	17. (original) The field effect device of claim 8, wherein said gate dielectric comprises
2	SiO ₂ .
1	18. (original) The field effect device of claim 8, wherein said gate dielectric comprises a
2	high-k dielectric material.
1	19. (original) The field effect device of claim 8, wherein said device is a Si based MOS
2	transistor.
4	20 (minimal) The Gold offers device of claim 10 subspain and device is an NTMOS
2	20. (original) The field effect device of claim 19, wherein said device is an NMOS transistor.
1	21. (currently amended) The field effect device of claim 20, wherein said NMOS
2	transistor has a threshold voltage between about 0.15V and 0.55V 0.36V and 0.45V.

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22. - 32. (canceled)

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2 .	at least one chip, wherein said chip comprises at least one semicon	auctor neta
3	effect device having a gate dielectric and a gate, wherein said gate compris	ses a compound
4	comprising Ta and N TaSiN disposed over said gate dielectric, wherein sa	uid compound
5	TaSiN has a resistivity below about 20mΩcm; and wherein in said compo	r und the
5	elemental ratio of N to Ta greater than about 0.9:1, and a workfunction b	etween about
7	4.31eV and 4.4eV.	

33. (currently amended) A processor, comprising:

34. (original) The processor of claim 33, wherein said processor is a digital processor.

35. (original) The processor of claim 33, wherein said processor comprises at least one analog circuit.

36. (new) The field effect device of claim, wherein TaSiN has a resistivity below about 20mΩcm.

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